Rewrite claim 5 as follows:

5. (Amended) A method for producing a silicon single crystal, wherein the silicon single crystal produced by the method according to claim 1 is processed into wafers, and the wafers are subjected to heat treatment at a temperature of 600 to 1000°C.

Rewrite claim 6 as follows:

6. (Amended) A method for producing a silicon single crystal, wherein the silicon single crystal produced by the method according to claim 2 is processed into wafers, and the wafers are subjected to heat treatment at a temperature of 600 to 1000°C.

A1 cont'd

Rewrite claim 7 as follows:

7. (Amended) A method for producing a silicon single crystal, wherein the silicon single crystal produced by the method according to claim 3 is processed into wafers, and the wafers are subjected to heat treatment at a temperature of 600 to 1000°C.

Rewrite claim 8 as follows:

8. (Amended) A method for producing a silicon single crystal, wherein the silicon single crystal produced by the method according to claim 4 is processed into wafers, and the wafers are subjected to heat treatment at a temperature of 600 to 1000°C.

Rewrite claim 11 as follows:

A2

11. (Amended) A method for producing a silicon epitaxial wafer formed an epitaxial layer on a surface of a silicon wafer produced from a CZ silicon single crystal pulled with doping with carbon and nitrogen in which the CZ silicon single

crystal is grown, wherein the CZ silicon single crystal is pulled to have carbon concentration, nitrogen concentration and oxygen concentration of 0.1 to 1 ppma, 1×10^{13} to 1×10^{14} number/cm^3 and 15 to 25 ppma, respectively, or 1 to 3 ppma, 1×10^{14} to 5×10^{15} number/cm^3 and 10 to 15 ppma, respectively.

Rewrite claim 13 as follows:

13. (Amended) A silicon epitaxial wafer formed an epitaxial layer on a surface of a silicon wafer produced from a CZ silicon single crystal pulled with doping with carbon and nitrogen in which the CZ silicon single crystal is grown, wherein the silicon wafer has carbon concentration, nitrogen concentration and oxygen concentration of 0.1 to 1 ppma, 1×10^{13} to 1×10^{14} atoms/cm^3 and 15 to 25 ppma, respectively, or 1 to 3 ppma, 1×10^{14} to 5×10^{15} atoms/cm^3 and 10 to 15 ppma, respectively.

Rewrite claim 15 as follows:

15. (Amended) A method for producing an annealed wafer formed a denuded zone in a surface layer of a CZ silicon wafer and having oxide precipitates of 1×10^{9} atoms/cm^3 in a bulk portion by performing a heat treatment to the CZ silicon wafer produced from a CZ silicon single crystal pulled with doping with carbon and nitrogen in which the CZ silicon single crystal is grown, wherein the CZ silicon single crystal is pulled to have carbon concentration, nitrogen concentration and oxygen concentration of 0.1 to 1 ppma, 1×10^{13} to 1×10^{14} atoms/cm^3 and 15 to 25 ppma, respectively, or 1 to 3 ppma, 1×10^{14} to 5×10^{15} atoms/cm^3 and 10 to 15 ppma, respectively.

Rewrite claim 17 as follows:

17. (Amended) An annealed wafer produced by performing a heat treatment to a CZ silicon wafer having carbon concentration, nitrogen concentration and oxygen concentration of 0.1 to 1 ppma, 1×10^{13} to 1×10^{14} atoms/cm^3 and 15 to 25

ppma, respectively, or 1 to 3 ppma, 1×10^{14} to 5×10^{15} atoms/cm^3 and 10 to 15 ppma, respectively, wherein BMD density in a bulk portion is 1×10^9 atoms/cm^3 or more.

A5 end